



650V SiC Schottky Diode

GP3D040A065U

| | |
|--------------------|-----------|
| VDC | 650 V |
| Q _C | 106 nC*** |
| I _F | 40 A*** |
| T _{j,max} | 175 °C |

Amp+™ Features

- Unipolar rectifier with surge current
- Zero reverse recovery current
- Fast, temperature-independent switching
- Avalanche tested to 135mJ*
- All parts tested to greater than 715V

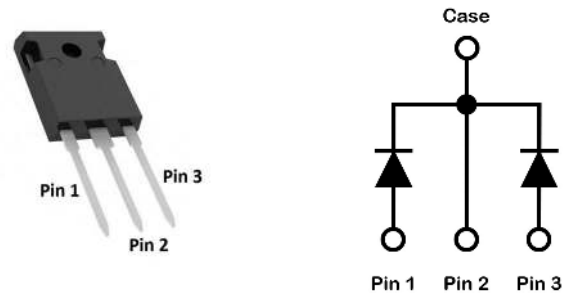
Amp+™ Benefits

- Near zero switching loss
- Higher efficiency
- Reduced heat sink requirements
- Easy to parallel

Amp+™ Applications

- Switch mode power supplies, UPS
- Power factor correction
- EV charging stations
- Output rectification

Package



| Part # | Package | Marking |
|--------------|-----------|-----------|
| GP3D040A065U | TO-247-3L | 3D040A065 |



Maximum Ratings, at T_j=25 °C, unless otherwise specified

| Characteristics Per Leg | Symbol | Conditions | Values | Unit |
|--|---------------------------------------|--|-----------|------------------|
| Continuous forward current | I _F ** | T _C =25 °C, T _J =175 °C | 55 | A |
| | | T _C =125 °C, T _J =175 °C | 28 | |
| | | T _C =150 °C, T _J =175 °C | 18 | |
| Surge non-repetitive forward current sine halfwave | I _{FSM} | T _C =25 °C, t _p =8.3 ms | 135 | A |
| | | T _C =110 °C, t _p =8.3 ms | 125 | |
| Non-repetitive peak forward current | I _{F,max} | T _C =25 °C, t _p =10 μs | 1100 | A |
| i ² t value | ∫i ² dt | T _C =25 °C, t _p =8.3 ms | 76 | A ² s |
| | | T _C =110 °C, t _p =8.3 ms | 65 | |
| Repetitive peak reverse voltage | V _{RRM} | T _J =25 °C | 650 | V |
| Diode dv/dt ruggedness | dv/dt | Turn-on slew rate, repetitive | 200 | V/ns |
| Power dissipation | P _{tot} ** | T _C =25 °C | 171 | W |
| Operating junction & storage temperature | T _j , T _{storage} | Continuous | -55...175 | °C |
| Soldering temperature | T _{solder} | Wave soldering leads | 260 | °C |
| Mounting torque | | M3 Screw | 1 | N-m |

Notes:

* EAS of 135 mJ is based on starting T_j = 25°C, L = 1.0 mH, I_{AS} = 16.43 A, V = 50 V.

** Typical R_{thjC} used

***Per Device

Electrical Characteristics, at T_j=25 °C, unless otherwise specified

| Characteristics Per Leg | Symbol | Conditions | Values | | | Unit |
|-------------------------|-----------------|--|--------|------|------|------|
| | | | min. | typ. | max. | |
| DC blocking voltage | V _{DC} | T _j =25 °C | 650 | - | - | V |
| Breakdown voltage | V _{BR} | I _R =660uA, T _j =25 °C | 715 | - | - | V |
| Diode forward voltage | V _F | I _F =20A, T _j =25 °C | - | 1.40 | 1.55 | V |
| | | I _F =20A, T _j =125 °C | - | 1.51 | - | |
| | | I _F =20A, T _j =175 °C | - | 1.64 | 1.90 | |
| Reverse current | I _R | V _R =650V, T _j =25 °C | - | 2 | 50 | μA |
| | | V _R =715V, T _j =25 °C | - | 7 | - | |
| | | V _R =650V, T _j =125 °C | - | 19 | - | |
| | | V _R =650V, T _j =175 °C | - | 72 | 500 | |
| Total capacitive charge | Q _C | V _R =400V, T _j =25 °C | - | 53 | - | nC |
| Total capacitance | C | V _R =1V, f=1 MHz | - | 866 | - | pF |
| | | V _R =200V, f=1 MHz | - | 102 | - | |
| | | V _R =400V, f=1 MHz | - | 78 | - | |

Thermal Characteristics

| Characteristics Per Leg | Symbol | Conditions | Values | | | Unit |
|-----------------------------------|-------------------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |
| Thermal resistance, junction-case | R _{thJC} | - | - | 0.88 | 1.05 | °C/W |

Typical Performance Per Leg

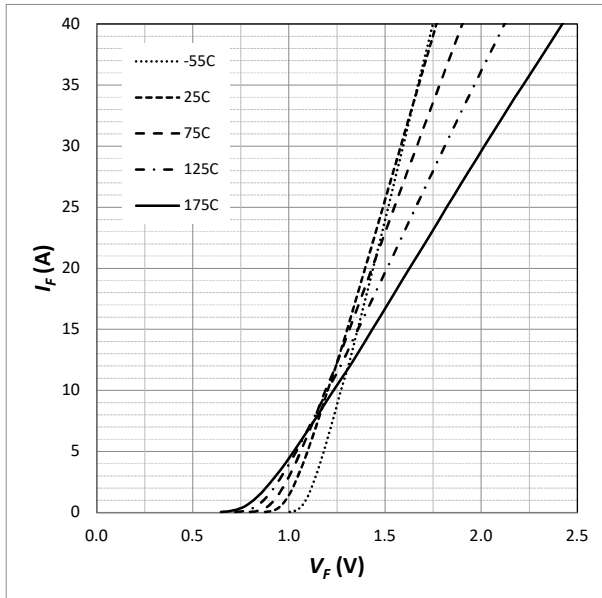


Fig. 1 Forward Characteristics (parameterized on T_j)

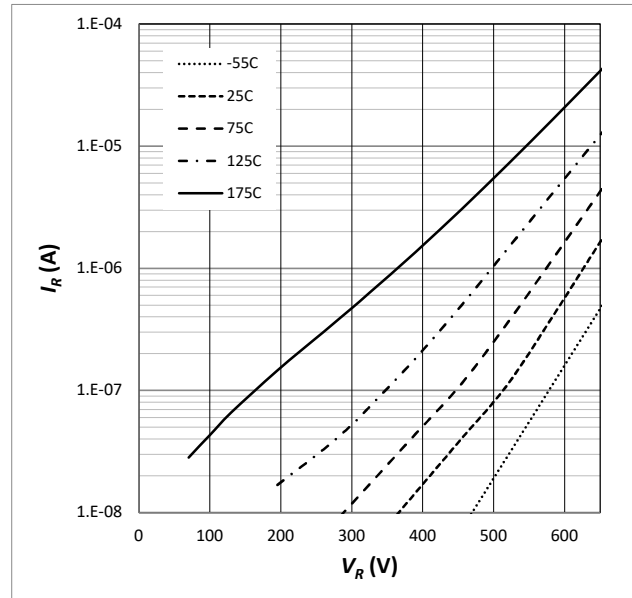


Fig. 2 Reverse Characteristics (parameterized on T_j)

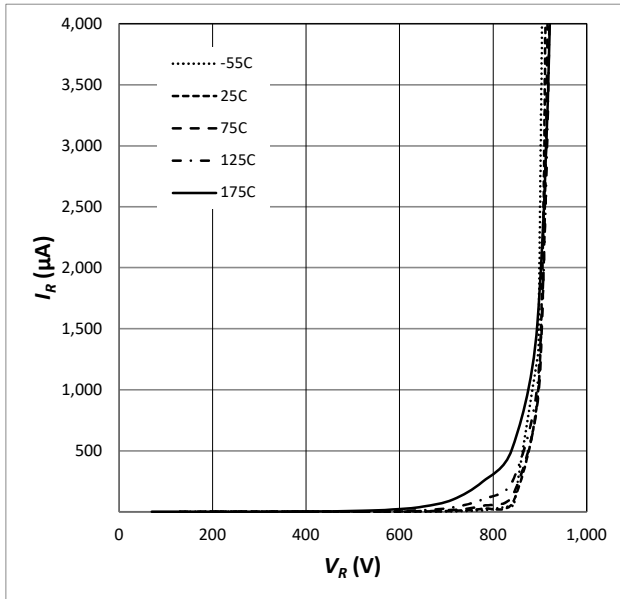


Fig. 3 Reverse Characteristics (parameterized on T_j)

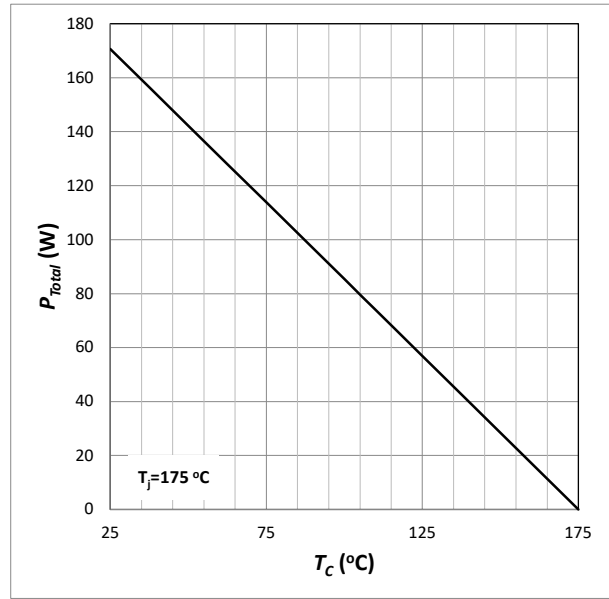


Fig. 4 Power Derating

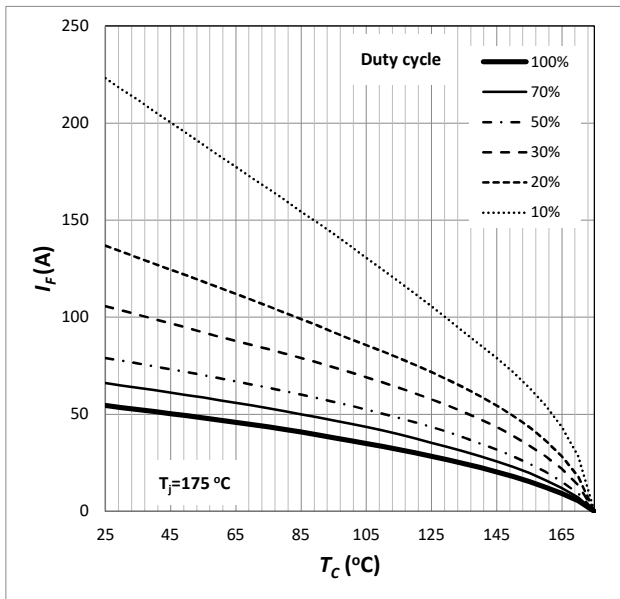


Fig. 5 Current Derating

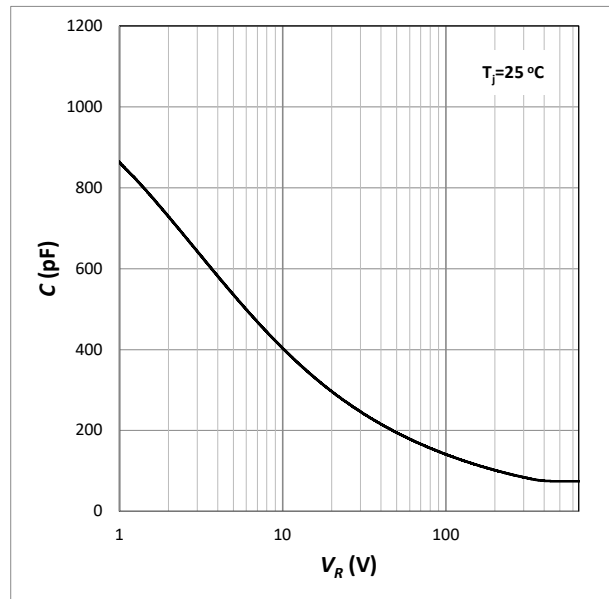


Fig. 6 Capacitance

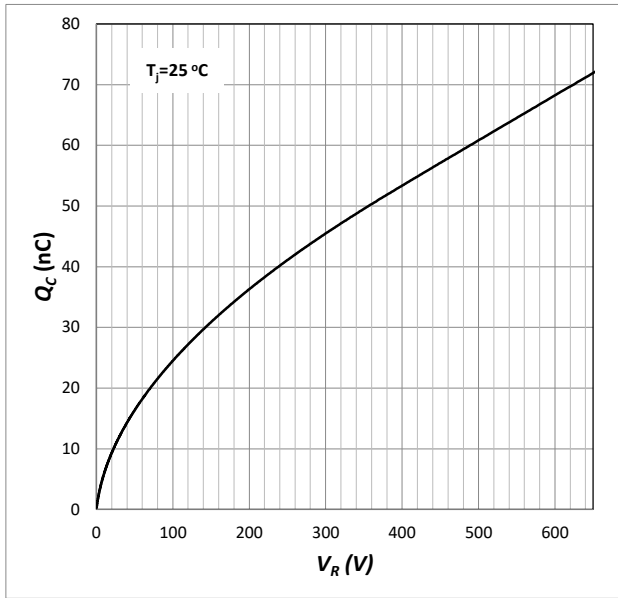


Fig. 7 Capacitive Charge

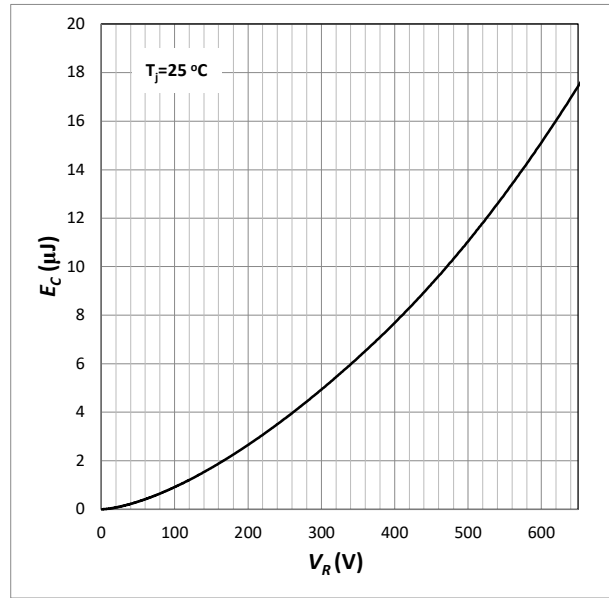


Fig. 8 Typical Capacitance Stored Energy

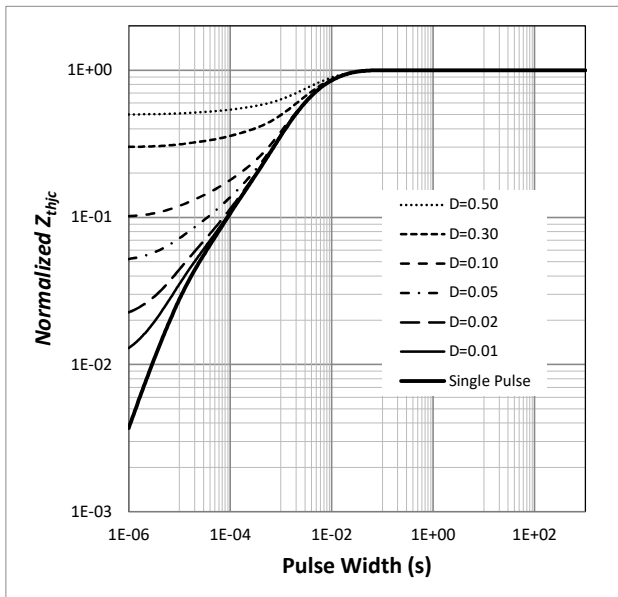


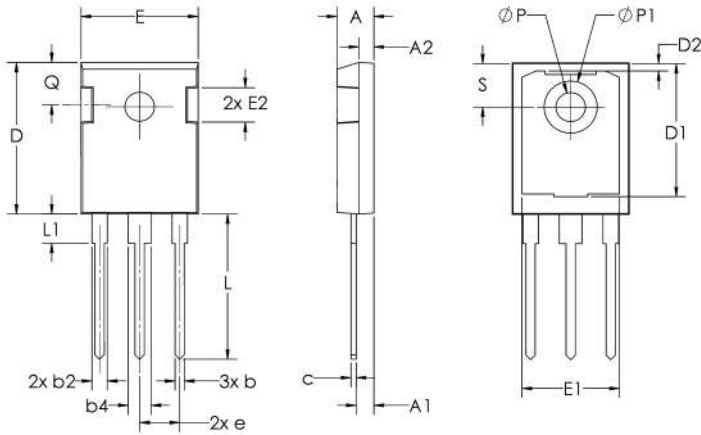
Fig. 9 Transient Thermal Impedance

650V SiC Schottky Diode

Amp+™

GP3D040A065U

Package Dimensions TO-247-3L



| Sym | Millimeters | | Inches | |
|--------|-------------|-------|-----------|-------|
| | Min | Max | Min | Max |
| A | 4.70 | 5.31 | 0.185 | 0.209 |
| A1 | 2.21 | 2.59 | 0.087 | 0.102 |
| A2 | 1.50 | 2.49 | 0.059 | 0.098 |
| b | 0.99 | 1.40 | 0.039 | 0.055 |
| b2 | 1.65 | 2.39 | 0.065 | 0.094 |
| b4 | 2.59 | 3.43 | 0.102 | 0.135 |
| c | 0.38 | 0.89 | 0.015 | 0.035 |
| D | 20.80 | 21.46 | 0.819 | 0.845 |
| D1 | 13.08 | 17.65 | 0.515 | 0.695 |
| D2 | 0.51 | 1.35 | 0.020 | 0.053 |
| E | 15.49 | 16.26 | 0.610 | 0.640 |
| E1 | 13.46 | 14.16 | 0.530 | 0.557 |
| E2 | 3.43 | 5.49 | 0.135 | 0.216 |
| e | 5.44 BSC | | 0.214 BSC | |
| L | 19.81 | 20.32 | 0.780 | 0.800 |
| L1 | 4.10 | 4.50 | 0.161 | 0.177 |
| phi P | 3.56 | 3.66 | 0.140 | 0.144 |
| phi P1 | 7.06 | 7.39 | 0.278 | 0.291 |
| Q | 5.39 | 6.20 | 0.212 | 0.244 |
| S | 6.04 | 6.30 | 0.238 | 0.248 |

Revision History

| Date | Revision | Notes |
|------------|----------|--|
| 12/20/2019 | 1.0 | Initial release of datasheet |
| 2/20/2020 | 1.1 | Using Rthjc typical for I _F and P _{tot} |
| 4/20/2021 | 1.2 | Updated forward voltage spec - valid for date codes after 2101 (YYWW format) |
| | | |

Notes**RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

REACH Compliance

REACH substances of high concern (SVHC) information is available for this product. Since the European Chemicals Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact our office at SemiQ Headquarters in Lake Forest, California to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

SemiQ Inc., reserves the right to make changes to the product specifications and data in this document without notice. SemiQ products are sold pursuant to SemiQ's terms and conditions of sale in place at the time of order acknowledgement.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control.

SemiQ makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SemiQ assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using SemiQ products.

To obtain additional technical information or to place an order for this product, please contact us. The information in this datasheet is provided by SemiQ. SemiQ reserves the right to make changes, corrections, modifications, and improvements of datasheet without notice.